# P-Channel 30-V (D-S) MOSFET

### **Key Features:**

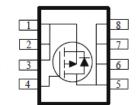
- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- Fast switching speed

### **Typical Applications:**

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY			
Vds (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)	
-30	9 @ V <sub>GS</sub> = -10V	-16	
	13 @ V <sub>GS</sub> = -4.5V	-13	







ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Limit	Units	
Drain-Source Voltage			-30	V	
Gate-Source Voltage	V <sub>GS</sub>	±20	V		
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =25°C		-16		
Continuous Drain Current	T <sub>A</sub> =70°C	I <sub>D</sub>	-13	А	
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	-50			
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	-4.9	А	
Power Dissinction <sup>a</sup>	T <sub>A</sub> =25°C	P <sub>D</sub>	3.1	W	
Power Dissipation <sup>a</sup>	T <sub>A</sub> =70°C	'D	2.2	vv	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Maximum	Units	
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	R <sub>eja</sub>	40	°C/W	
	Steady State	ιν <sub>θ</sub> ja	80	C/W	

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

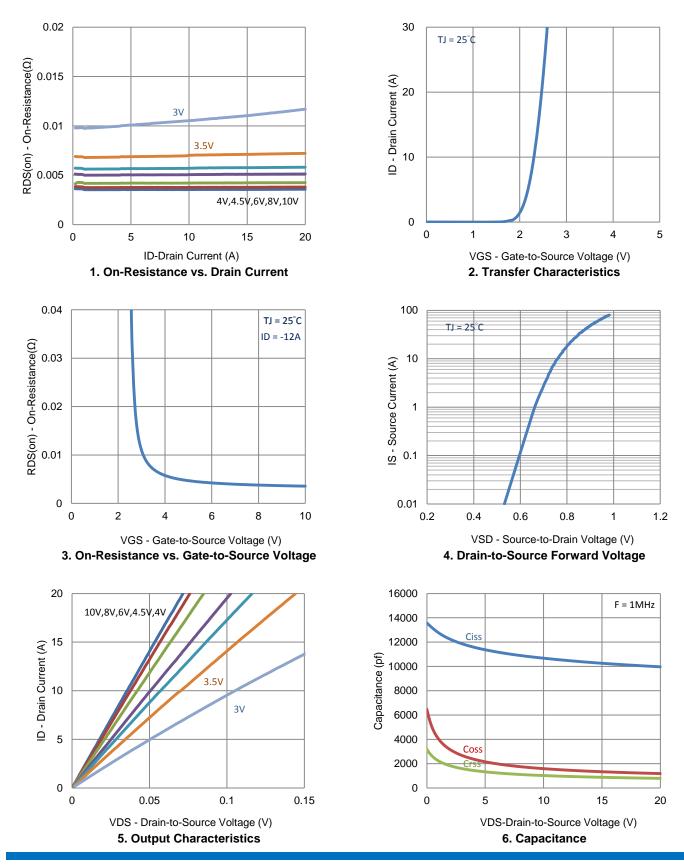
## **Electrical Characteristics**

Parameter	Symbol	Test Conditions	Min	Тур	Мах	Unit	
Static							
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-1			V	
Gate-Body Leakage	I <sub>GSS</sub>				±100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$			-1 uA -25		
	IDSS	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$					
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = -5 V, V_{GS} = -10 V$	-25			А	
Drain-Source On-Resistance <sup>a</sup>	r	$V_{GS}$ = -10 V, $I_{D}$ = -12 A			9	mΩ	
Drain-Source On-Resistance	r <sub>DS(on)</sub>	$V_{GS}$ = -4.5 V, $I_{D}$ = -9.6 A			13		
Forward Transconductance <sup>a</sup>	<b>g</b> <sub>fs</sub>	$V_{DS} = -15 \text{ V}, \text{ I}_{D} = -12 \text{ A}$		32		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{S} = -2.5 \text{ A}, V_{GS} = 0 \text{ V}$		-0.71		V	
	Dynamic <sup>b</sup>						
Total Gate Charge	Qg	V <sub>DS</sub> = -15 V, V <sub>GS</sub> = -4.5 V,		118			
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = -13 V, V_{GS} = -4.3 V,$ $I_{D} = -12 A$		33		nC	
Gate-Drain Charge	$Q_gd$			46			
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DS</sub> = -15 V, R <sub>I</sub> = 1.3 Ω,		11			
Rise Time	t <sub>r</sub>	$V_{DS} = -13 V, R_{L} = -1.3 \Omega_{2},$ $I_{D} = -12 A,$		30		<b>DC</b>	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{\text{GEN}} = -10 \text{ V}, \text{ R}_{\text{GEN}} = 6 \Omega$		347		ns	
Fall Time	t <sub>f</sub>	$v_{\text{GEN}} = -10 v$ , $N_{\text{GEN}} = 0.02$		193			
Input Capacitance	C <sub>iss</sub>			10260			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -15 V, V_{GS} = 0 V, f = 1 Mhz$		1334		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			876			

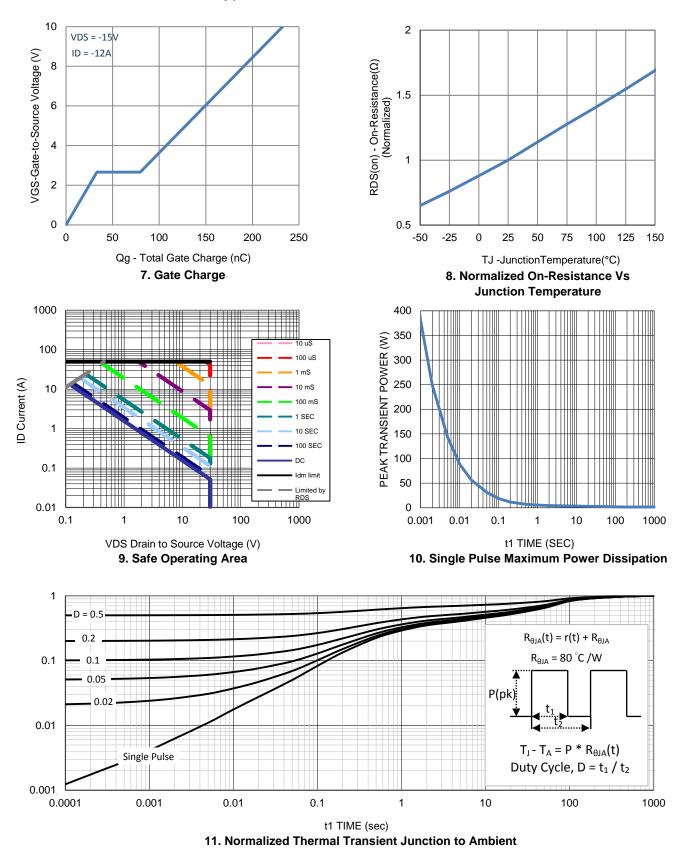
#### Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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**Typical Electrical Characteristics** 

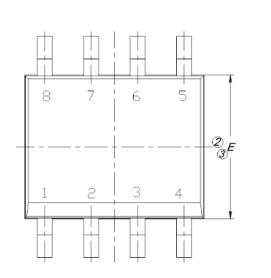


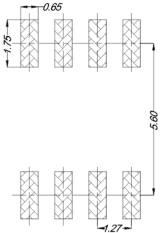
### **Typical Electrical Characteristics**

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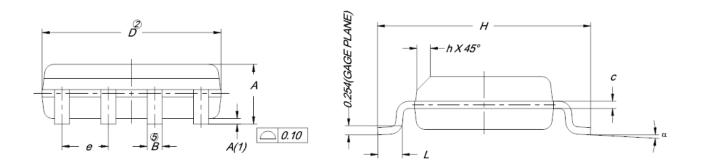
### **Package Information**

Land Pattern (Only for Reference)





	MILLIMETERS				
DIM.	MIN. NOM.		MAX.		
А	1.35	1.55	1.75		
A(1)	0.10	0.18	0.25		
В	0.38	0.45	0.51		
С	0.19	0.22	0.25		
D	4.80	4.90	5.00		
E	3.80	3.90	4.00		
е	1.27 BSC				
н	5.80	6.00	6.20		
L	0.50	0.72	0.93		
α	0°	4°	8°		
h	0.25	0.38	0.50		



Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Tie Bar Burrs, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.
- 4. The Package Top May Be Smaller Than The Package Bottom.
- Dimension "B" Does Not Include Dambar Protrusion. Allowable Dambar Protrusion Shall Be 0.08 mm Total In Excess Of "B" Dimension At Maximum Material Condition. The Dambar Cannot Be Located On The Lower Radius Of The Foot.